

PSMN028-100YS

N-channel LFPAK 100V 27.5 m Ω standard level MOSFET

Rev. 02 — 30 March 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in LFPAK package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Advanced TrenchMOS provides low RDSon and low gate charge
- High efficiency gains in switching power converters
- Improved mechanical and thermal characteristics
- LFPAK provides maximum power density in a Power SO8 package

1.3 Applications

- DC-to-DC converters
- Lithium-ion battery protection
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	-	-	42	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	89	W
Tj	junction temperature		-55	-	175	°C
Avalanc	he ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $I_D = 34 \text{ A}; V_{sup} \le 100 \text{ V};$ unclamped; $R_{GS} = 50 \Omega$	-	-	68	mJ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$	-	10.3	-	nC
$Q_{G(tot)}$	total gate charge	V _{DS} = 50 V; see <u>Figure 15</u> and <u>16</u>	-	33	-	nC



Table 1. Quick reference ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static ch	aracteristics					
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure } 13}{\text{ constant}}$	-	-	52	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 14}{\text{Figure } 14}$	-	21.4	27.5	mΩ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		_
2	S	source	mb	D
3	S	source		
4	G	gate	[Q]	<u> </u>
mb	D	mounting base; connected to drain	1 2 3 4	mbb076 Ś
			SOT669 (LFPAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN028-100YS	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}$	-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	100	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see <u>Figure 1</u>	-	30	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u>	-	42	Α
I _{DM}	peak drain current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$; see Figure 3	-	137	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	89	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-di	ain diode				
Is	source current	T _{mb} = 25 °C; see <u>Figure 4</u>	-	42	Α
I _{SM}	peak source current	t _p ≤ 10 μs; pulsed; T _{mb} = 25 °C	-	137	Α
Avalanch	e ruggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 34 A; V_{sup} ≤ 100 V; unclamped; R_{GS} = 50 Ω	-	68	mJ

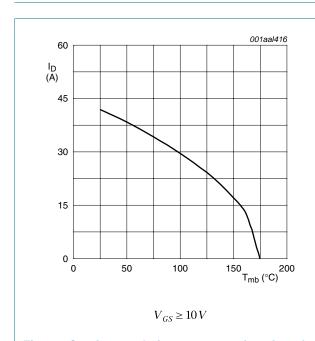


Fig 1. Continuous drain current as a function of mounting base temperature

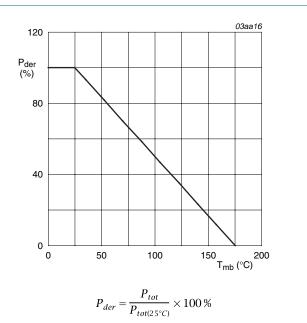
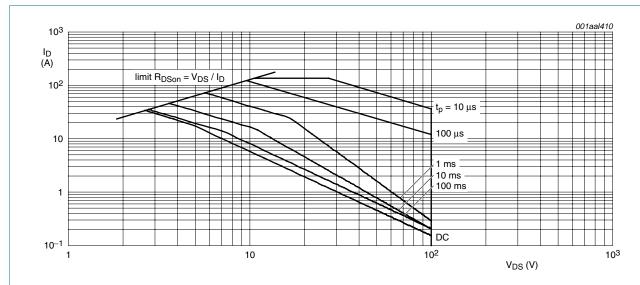


Fig 2. Normalized total power dissipation as a function of mounting base temperature



 $T_{mb} = 25 \,^{\circ}C; I_{DM}$ is single pulse

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

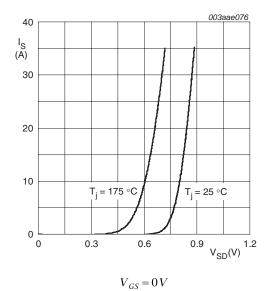
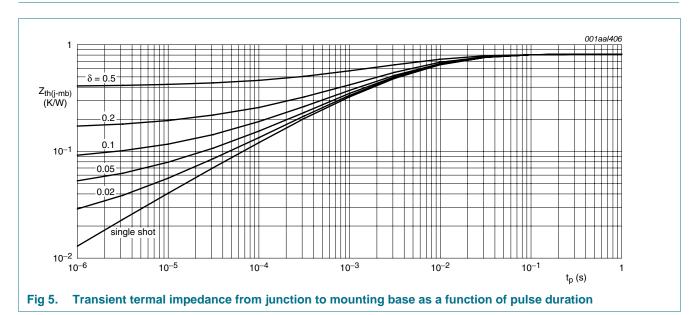


Fig 4. Source current as a function of source-drain voltage; typical values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	0.81	1.68	K/W



6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	90	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold	$I_D = 1 \text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 175 \text{ °C}$; see Figure 11	1	-	-	V
	voltage	I_D = 1 mA; V_{DS} = V_{GS} ; T_j = 25 °C; see <u>Figure 12</u> and <u>11</u>	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see <u>Figure 11</u>	-	-	4.7	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$	-	-	50	μΑ
		$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	2	μΑ
I_{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nΑ
R_{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 13	-	-	52	mΩ
		$V_{GS} = 10 \text{ V; } I_D = 15 \text{ A; } T_j = 175 \text{ °C;}$ see Figure 13	-	49.9	74.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C};$ see Figure 14	-	21.4	27.5	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz	-	0.5	1.5	Ω
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 15</u> and <u>16</u>	-	33	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	25	-	nC
Q_{GS}	gate-source charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 15</u> and <u>16</u>	-	7.2	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 15 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see <u>Figure 15</u>	-	5	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		-	2.2	-	nC
Q_{GD}	gate-drain charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V; see <u>Figure 15</u> and <u>16</u>	-	10.3	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$V_{DS} = 50 \text{ V}$; see <u>Figure 15</u> and <u>16</u>	-	4.1	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 °C;$	-	1634	-	pF
C _{oss}	output capacitance	see Figure 17	-	132	-	pF
C _{rss}	reverse transfer capacitance		-	85	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 3.3 \Omega; V_{GS} = 10 \text{ V};$	-	15	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega; T_j = 25 °C$	-	14	-	ns
t _{d(off)}	turn-off delay time		-	33	-	ns

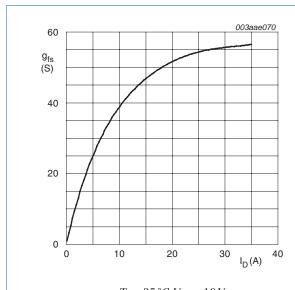
Source-drain diode

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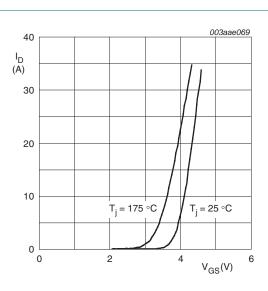
Table 6. Characteristics ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 4}}{}$	-	8.0	1.2	V
t _{rr}	reverse recovery time	$I_S = 5 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$; $V_{GS} = 0 \text{ V}$;	-	48.7	-	ns
Qr	recovered charge	$V_{DS} = 50 \text{ V}$	-	95.7	-	nC



 $T_j = 25 \,^{\circ}C; V_{DS} = 10 \, V$

Fig 6. Forward transconductance as a function of drain current; typical values



 $V_{DS} > I_D \times R_{DSon}$

Fig 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

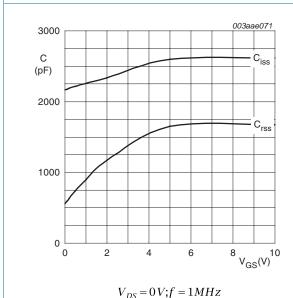


Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

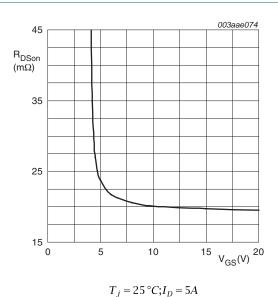


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values.

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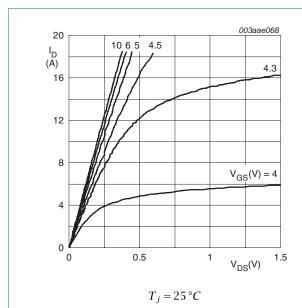


Fig 10. Output characteristics: drain current as a function of drain-source voltage; typical values

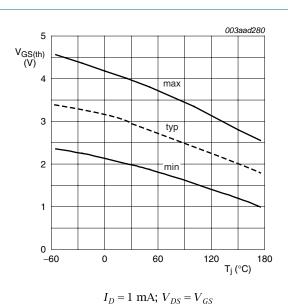


Fig 11. Gate-source threshold voltage as a function of junction temperature

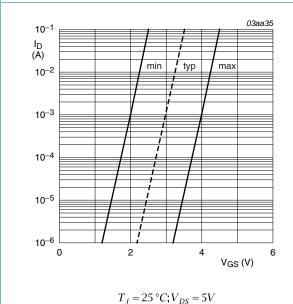


Fig 12. Sub-threshold drain current as a function of gate-source voltage

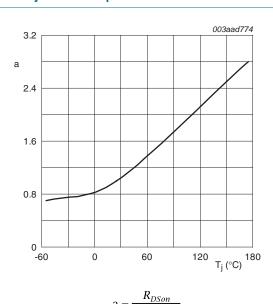


Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

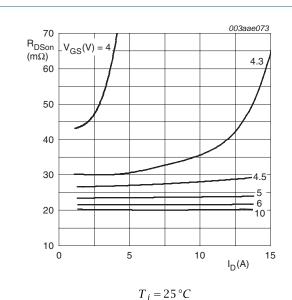


Fig 14. Drain-source on-state resistance as a function of drain current; typical values

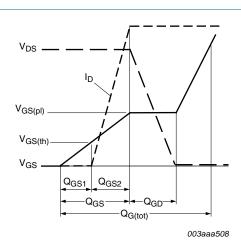


Fig 15. Gate charge waveform definitions

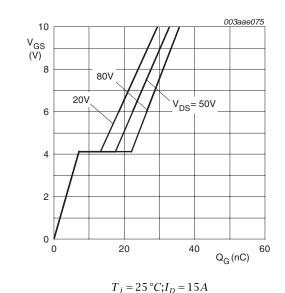
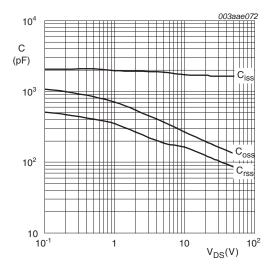
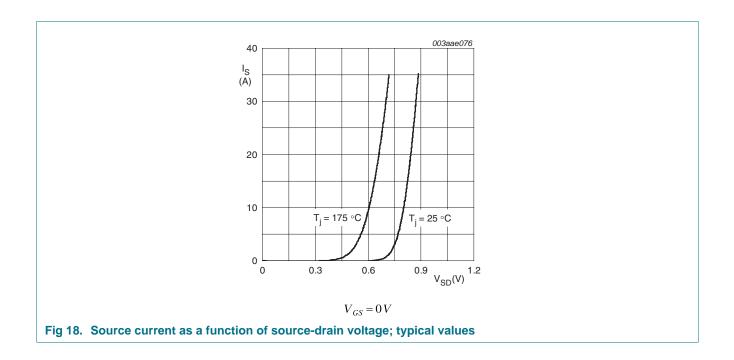


Fig 16. Gate-source voltage as a function of gate charge; typical values



 $V_{GS} = 0V; f = 1MHz$

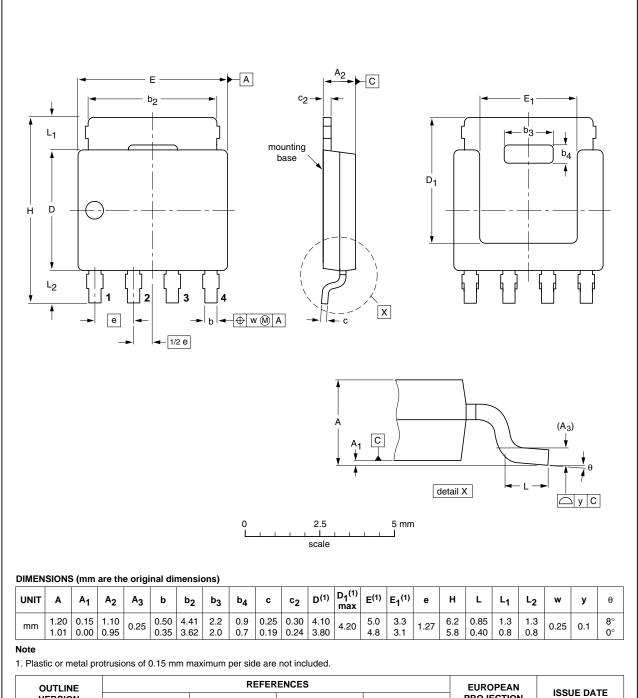
Fig 17. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



7. Package outline

Plastic single-ended surface-mounted package (LFPAK); 4 leads

SOT669



OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT669		MO-235			$ \ \ \bigoplus \big($	04-10-13 06-03-16

Fig 19. Package outline SOT669 (LFPAK)

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN028-100YS_2	20100330	Product data sheet	-	PSMN028-100YS_1
Modifications:	 Status char 	nged from objective to pr	oduct.	
	 Various cha 	anges to content.		
PSMN028-100YS_1	20100210	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nexperia.com.

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PSMN028-100YS

Nexperia

N-channel LFPAK 100V 27.5 mΩ standard level MOSFET

11. Contents

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